ROHS Compliance, The RF MOSFET Line, Enhancement Mode

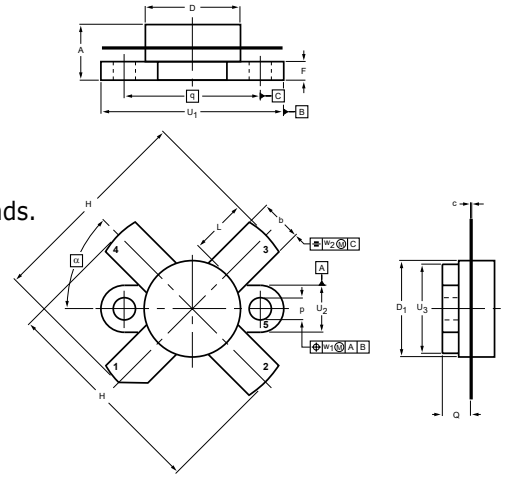
HG Semiconductors

BLF147

Silicon MOS N-CHANNEL RF POWER TRANSISTOR

DESCRIPTION

Silicon N-channel enhancement mode vertical D-MOS transistor. Designed for broadband HF and VHF applications.The high power, high gain and broadband performance of this device makes possible solid state transmitters for FM broadcast or TV channel frequency bands.



1.Drain
2.Source
3.Gate
4.Source
5.FIN

FEATURES

- Output Power: 150 W
- Power Gain: 14 dB Typ@108M, 28V
  17 dB Min@30M , 28V
- Efficiency: 35% Min

DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANCE.

UNIT	A	b	c	D	D_1	F	H	L	p	Q	q	U_1	U_2	U_3	w_1	w_2	α
mm	7.27 6.17	5.82 5.56	0.16 0.10	12.86 12.59	12.83 12.57	2.67 2.41	28.45 25.52	7.93 6.32	3.30 3.05	4.45 3.91	18.42	24.90 24.63	6.48 6.22	12.32 12.06	0.51	1.02	45°
inches	0.286 0.243	0.229 0.219	0.006 0.004	0.506 0.496	0.505 0.495	0.105 0.095	1.120 1.005	0.312 0.249	0.130 0.120	0.175 0.154	0.725	0.98 0.97	0.255 0.245	0.485 0.475	0.02	0.04	

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Drain–Source Voltage	V_{DSS}	65	V
Gate–Source Voltage	$\pm V_{GS}$	20	V
Drain Current — Continuous	I_D	25	A
Total Device Dissipation	P_D	230	W
Junction Temperature	T_J	200	°C
Storage Temperature Range	T_{STG}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain–Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=100mA,V_{GS}=0	65	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V,V_{DS}=28V	-	-	5	mAdc
Gate–Source Leakage Current	I_{GSS}	V_{GS}=20V,V_{DS}=0V	-	-	1	uAdc
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = 10 V, I_D = 200mA	2.0	-	4.5	V
Forward Transconductance	gfs	V_{DS} = 10 V, I_D = 8A	5	7.5	-	mhos
Input Capacitance	Ciss	V_{DS} = 28 V,V_{GS} = 0 V, f = 1.0 MHz	-	460	-	pF
Output Capacitance	Coss		-	320	-	pF
Reverse Transfer Capacitance	Crss		-	30	-	pF
Common Source Power Gain	G_{PS}	V_{DD}=28V,P_{OUT}=150W, f=30; 30.001MHz,I_{DQ} = 250 mA	17.0	-	-	dB
Drain Efficiency	η_D		35	-	-	%
Common Source Power Gain	G_{PS}	V_{DD}=28V,P_{OUT}=150W, f=108MHz,I_{DQ} = 250mA	-	14.0	-	dB
Drain Efficiency	η_D		-	70.0	-	%
Intermodulation Distortion	IMD	V_{DD} = 28 V, Pout = 150 W (PEP),f1 = 30 MHz, f2 = 30.001 MHz, I_{DQ} = 1 A	-	-	-30	dB

Note : Above parameters , ratings , limits and conditions are subject to change.